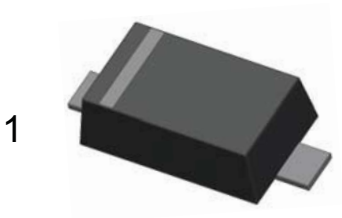
Schottky Diodes

1N5817W ~ 1N5819W

■ Features

- Low power loss, high efficiency
- High current capability
- Low forward voltage drop
- High Surge Capability

SOD-123F



Top View

PIN DESCRIPTION

PIN	DESCRIPTION
1	Cathode
2	Anode

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	1N5817W	1N5818W	1N5819W	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	20	30	40	V
RMS Voltage	V_{RMS}	14	21	28	
DC Blocking Voltage	V_{DC}	20	30	40	
Forward Voltage @ I_F=1A	V_F	0.45	0.55	0.6	
Forward Voltage @ I_F=3.1A		0.75	0.875	0.9	
Average Forward Rectified Current @ T_L=90℃	I_{FAV}	1			A
Non-Repetitive Peak Forward Surge Current @8.3ms	I_{FSM}	25			
Reverse Voltage Leakage Current Ta = 25℃	I_R	1			mA
Reverse Voltage Leakage Current Ta = 100℃		10			
Typical Junction Capacitance	C_J	110			pF
Junction Temperature	T_J	125			℃
Storage Temperature range	T_{stg}	-55 to 125			

■ Marking

NO.	1N5817W	1N5818W	1N5819W
Marking	12A	13A	14A

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■ Typical Characterisitics

Fig.1 Forward Current Derating Curve

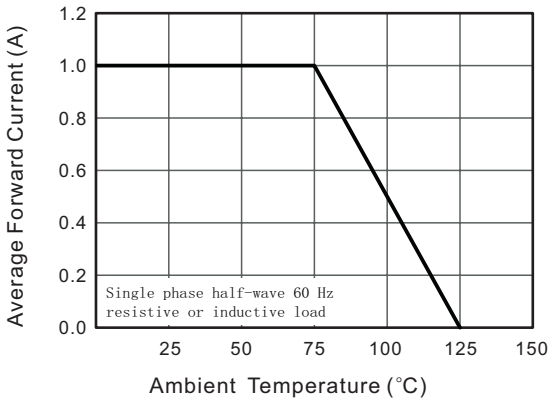


Fig.2 Typical Reverse Characteristics

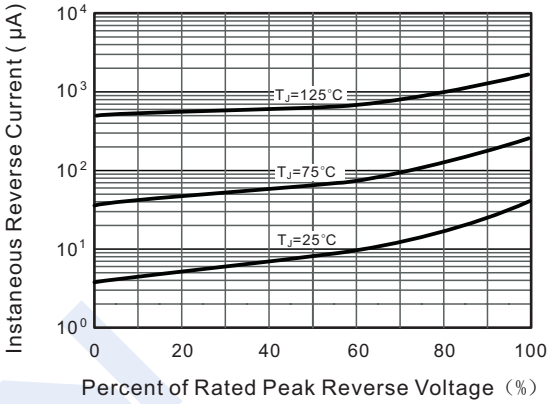


Fig.3 Typical Forward Characteristic

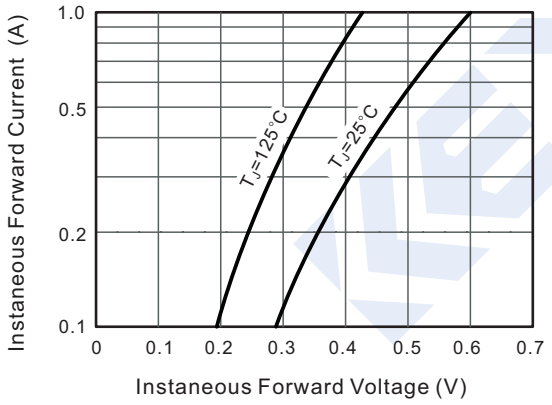


Fig.4 Typical Junction Capacitance

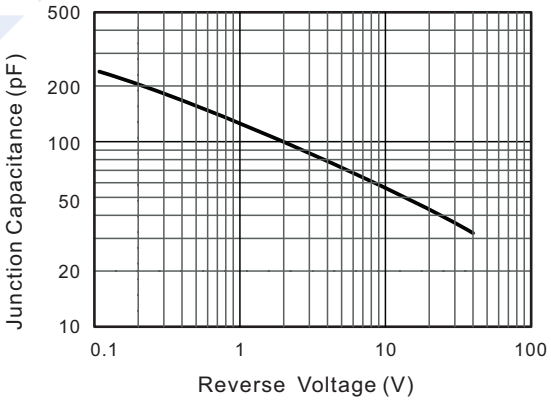


Fig.5 Maximum Non-Repetitive Peak Forward Surage Current

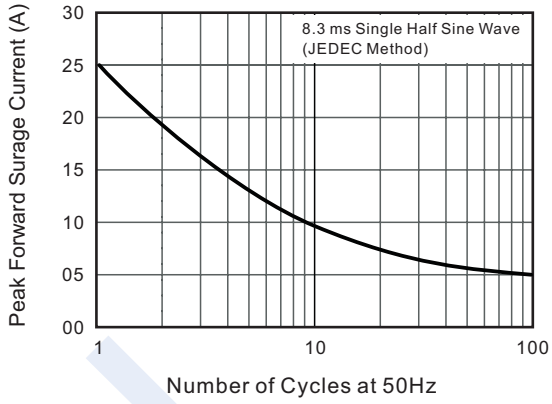
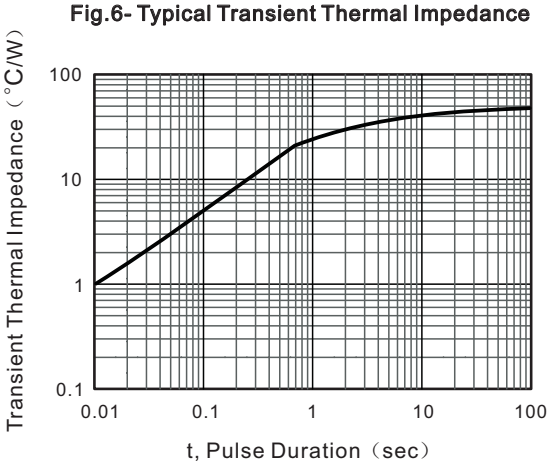


Fig.6- Typical Transient Thermal Impedance

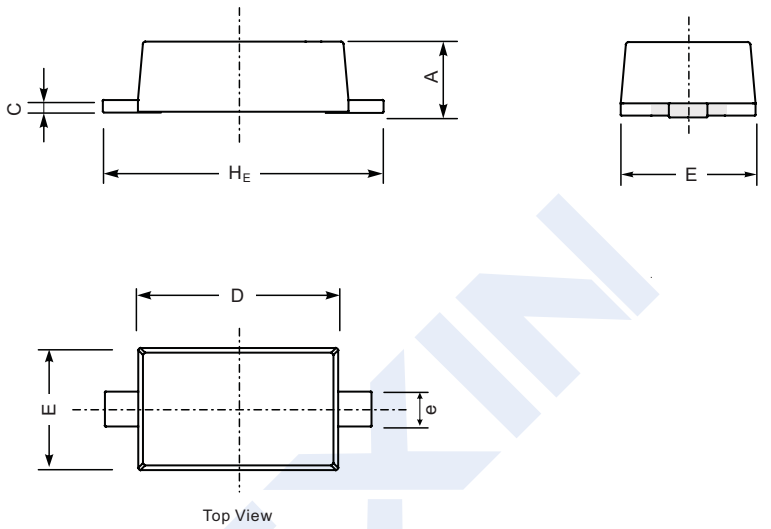


Schottky Diodes

1N5817W ~ 1N5819W

■ Package Outline Dimensions

Plastic surface mounted package; 2 leads SOD-123F



UNIT		A	C	D	E	e	H_E
mm	max	1.0	0.20	2.7	1.7	0.7	3.7
	min	0.8	0.05	2.5	1.5	0.5	3.3
mil	max	39	8	106	67	28	146
	min	31	2	98	59	20	130

■ The Recommended Mounting Pad Size